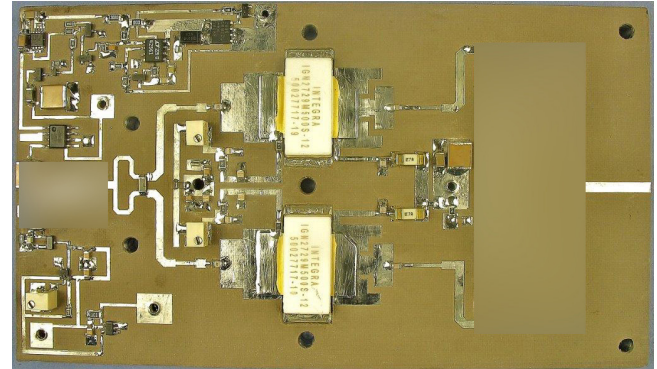


S-Band, GaN/SiC, RF Power Amplifier Pallet

2.7 - 2.9 GHz | 1kW typ | 54% Efficiency typ | 12 dB Gain typ | 50 V | 300µs Pulse Length, 10% Duty Cycle

IGNP2729M1KW-GPS is a high power GaN-on-SiC RF power amplifier pallet that has been designed to suit the unique needs of S band radar systems. It operates over the full 2.7 - 2.9 GHz frequency range. Under 300µs, 10% duty cycle pulse conditions, it supplies a minimum of 1 kW of peak output power, with typically >12 dB of gain and 54% efficiency. It operates from a 50 V supply voltage.



IGNP2729M1KW-GPS

FEATURES

- GaN on SiC HEMT Technology
- Output Power >1 kW
- Fully matched to 50Ω
- High Efficiency - up to 54%
- Incorporates Gate Pulsing & Sequencing (GPS) fully automatic, fail-safe bias circuitry
- 100% RF Tested under 300µs, 10% duty cycle pulse conditions

APPLICATIONS

- S-band Radar Systems

Table 1. RF Electrical Characteristics (Case temperature = 25 +/- 5 °C unless otherwise stated)

Parameter	Symbol	Min	Typ	Max	Units	Test Conditions
RF Output Power	$P_{OUT,RF}$	1000			W	$P_{IN} = 74W$ $f = 2.7, 2.8, 2.9 \text{ GHz}$ 300µs pulse length, 10% duty cycle $V_{DS} = 50V, I_{DS} = 200mA,$
Gain	G	11.3			dB	
Drain Efficiency	η	50			%	
Input Return Loss	IRL	10			dB	
Pulse Droop	D			-0.6	dB	
Load Mismatch Stability	VSWR-S	2:1				
VSWR Withstand	VSWR-LMT	3:1				

Note: Consult Integra Technologies Application Note 001 for information on how RF output power and pulse droop are measured.

Table 2. Absolute Maximum Ratings (Not Simultaneous)

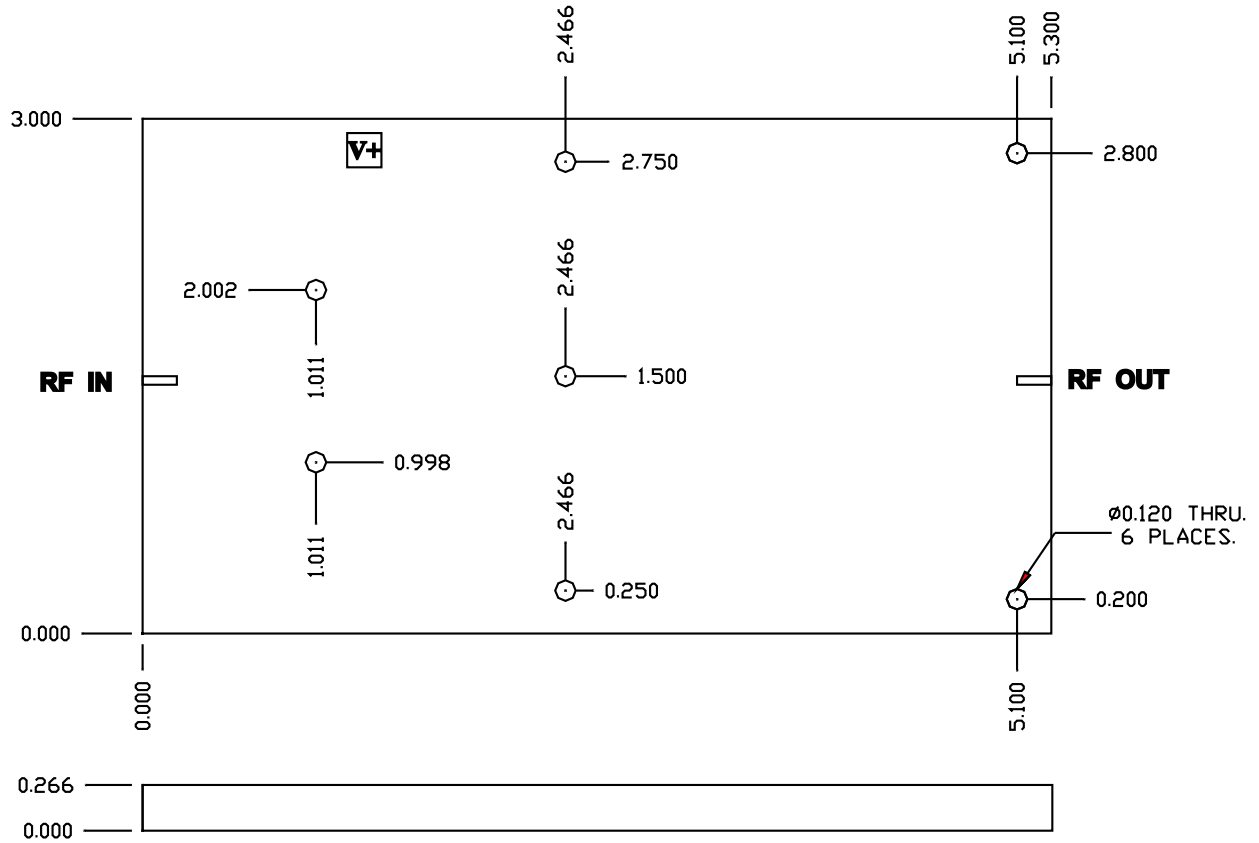
Parameter	Symbol	Value	Units	Test Conditions
DC Drain-Source Supply Voltage	V_{DS}	50	V	25 °C
DC Drain Current	I_D	50	A	25 °C
RF Input Power	$P_{RF,IN}$	74	W	25 °C
Operating Ambient Temperature	T_{AMB}	-40 to +85	°C	
Storage Temperature	T_{STG}	-55 to +150	°C	
Module Soldering temperature	T_{SOLDER}	260	°C	<50 sec at >200 °C
Operating Channel Temperature	T_{CH}	+200	°C	

Note: Operation outside the limits given in this table may cause permanent damage

Table 3. Thermal Resistance (Case temperature = 25 °C unless otherwise stated)

Parameter	Symbol	Min	Typ	Test Conditions
Peak Thermal Resistance, Channel to underneath side of module	R_{TH}		TBD	$P_{OUT} = 1000W$ $f = 2.8 GHz$ 300µs pulse length, 10% duty cycle $V_{DS} = 50V, I_{DS} = 200mA$

DIMENSIONS (INCHES)



ESD Rating

Parameter	Rating	Standard
ESD Human Body Model (HBM)	TBD	ESDA/JEDEC JS-001-2012
ESD Charged Device Model (CDM)	TBD	JEDEC JESD22-C101F
Moisture Sensitivity Level (MSL)	0	IPC/JEDEC J-STD-020

DEFINITIONS:

DATA SHEET STATUS

Advanced Specification - This data sheet contains Advanced specifications.

Preliminary Specification - This data sheet contains specifications based on preliminary measurements and data.

Final Specification - This data sheet contains final product specifications.

MAXIMUM RATINGS Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.

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